

General Description

The WSP4447 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSP4447 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

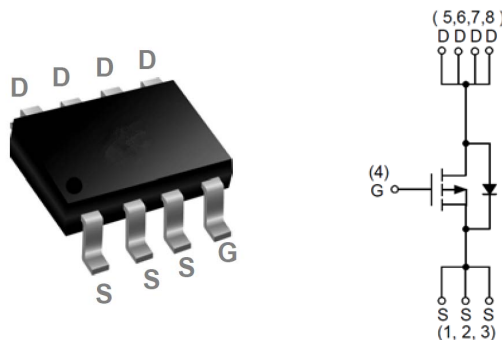
Product Summary

BVDSS	R _{DS(on)}	I _D
-40V	13mΩ	-11A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-11	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-9.0	A
I _{DM} ^a	300μs Pulsed Drain Current (V _{GS} =-10V)	-44	A
E _{AS} ^b	Avalanche Energy, Single pulse (L=0.1mH)	54	mJ
I _{AS} ^b	Avalanche Current, Single pulse (L=0.1mH)	-33	A
P _D @T _A =25°C	Total Power Dissipation ⁴	2.0	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	75	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	24	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.018	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-13A	---	13	16	mΩ
		V _{GS} =-4.5V, I _D =-5A	---	18	26	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.4	-1.9	-2.4	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	5.04	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-32V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	---	18	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-10V, I _D =-11A	---	32	---	nC
Q _{gs}	Gate-Source Charge		---	5.2	---	
Q _{gd}	Gate-Drain Charge		---	8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-20V, V _{GS} =-10V, R _G =6Ω, I _D =-1A, R _L =20Ω	---	14	---	ns
T _r	Rise Time		---	12	---	
T _{d(off)}	Turn-Off Delay Time		---	41	---	
T _f	Fall Time		---	22	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1500	---	pF
C _{oss}	Output Capacitance		---	235	---	
C _{rss}	Reverse Transfer Capacitance		---	180	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	-3.0	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	-18	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.1	V
t _{rr}	Reverse Recovery Time	I _F =-11A, dI/dt=100A/μs, T _J =25°C	---	24	---	nS
Q _{rr}	Reverse Recovery Charge		---	18	---	nC

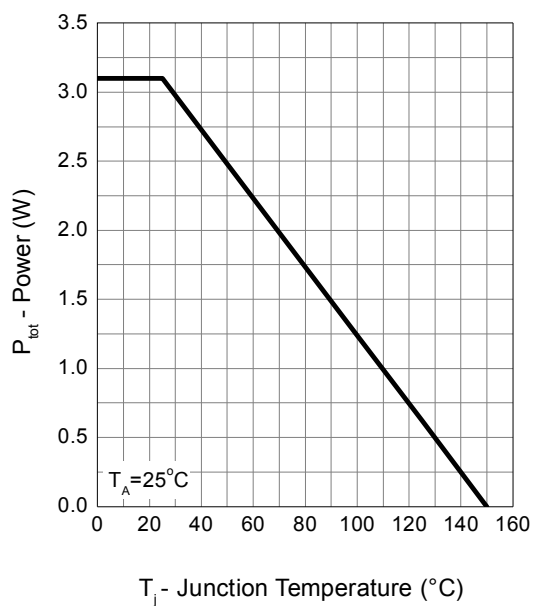
Note

1, Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.

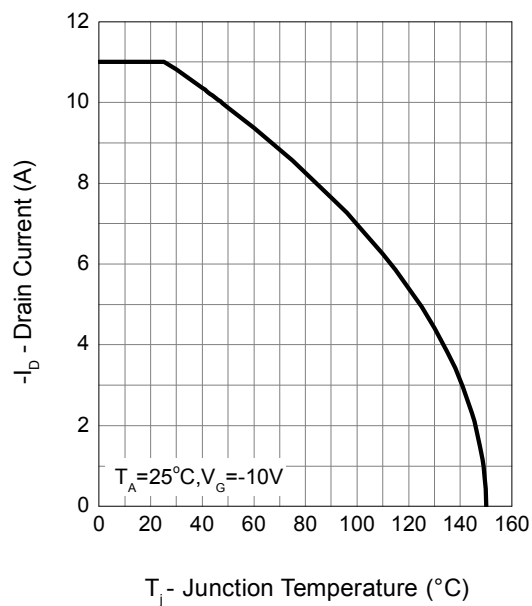
2, Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

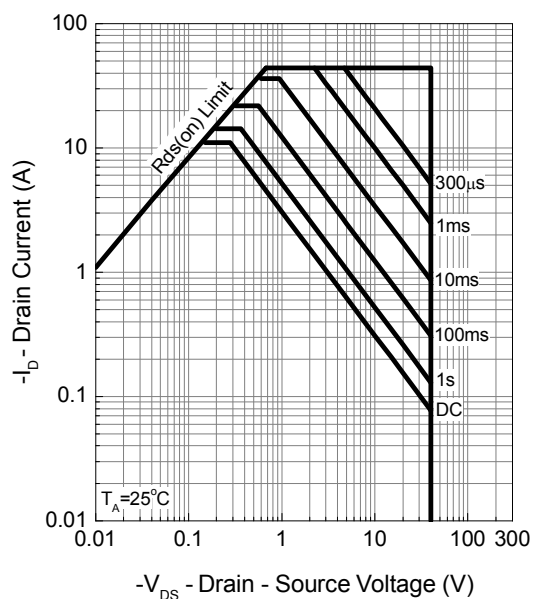
Power Dissipation



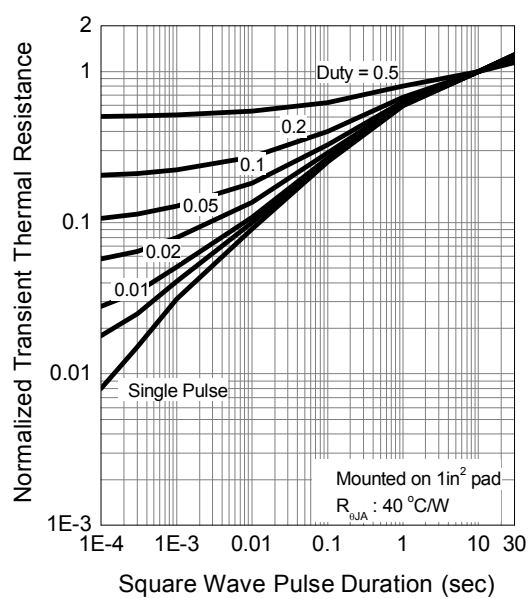
Drain Current



Safe Operation Area

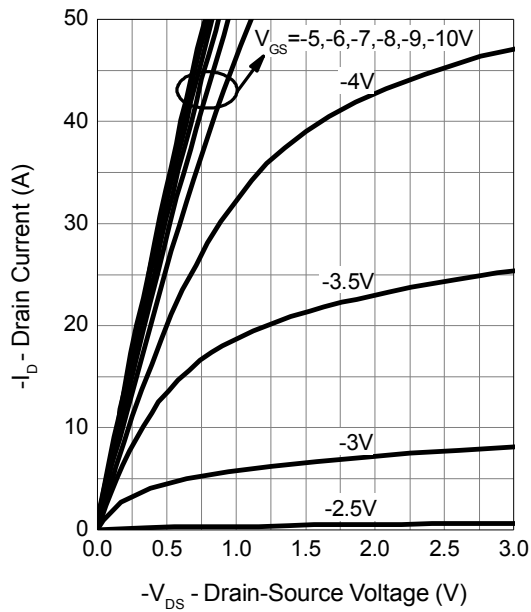


Thermal Transient Impedance

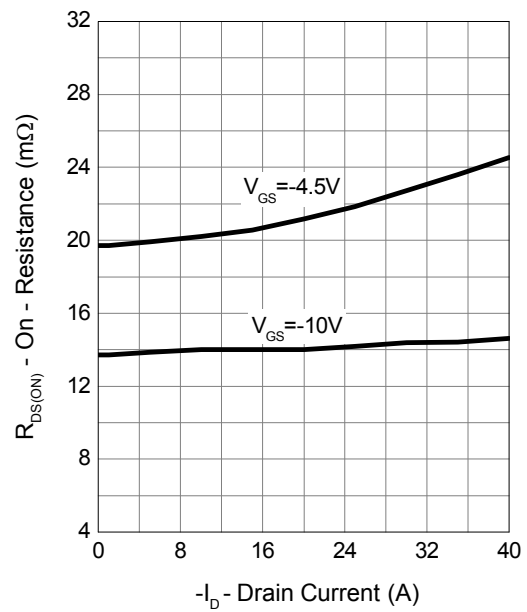


Typical Operating Characteristics (Cont.)

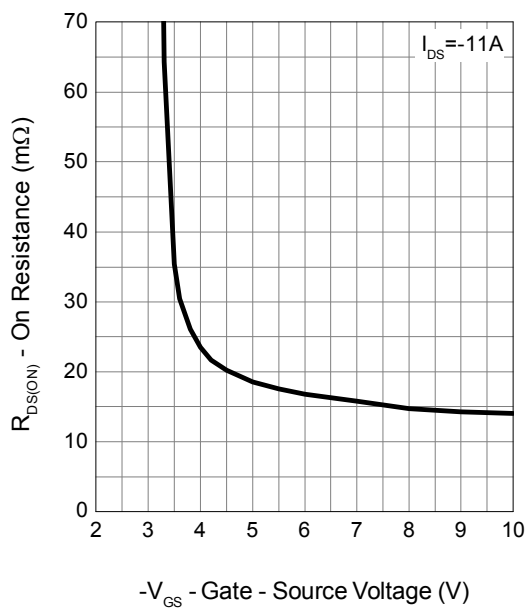
Output Characteristics



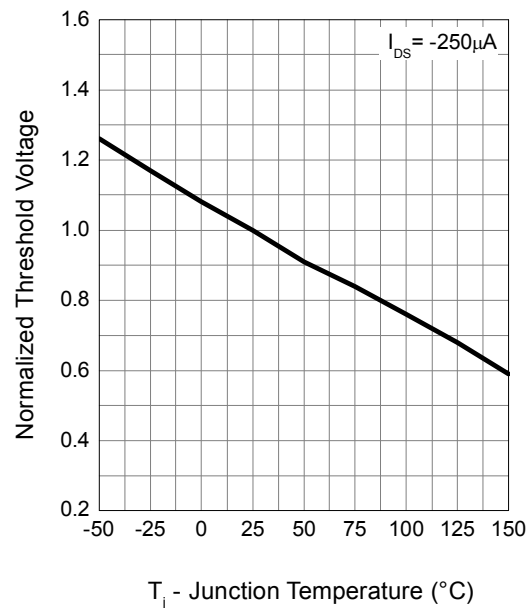
Drain-Source On Resistance



Gate-Source On Resistance

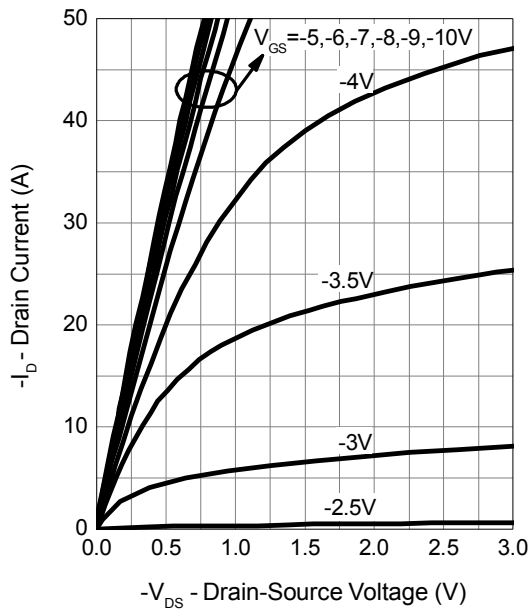


Gate Threshold Voltage

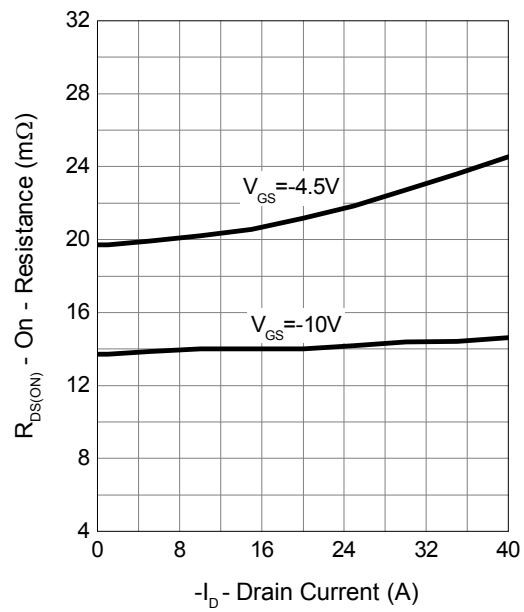


Typical Operating Characteristics (Cont.)

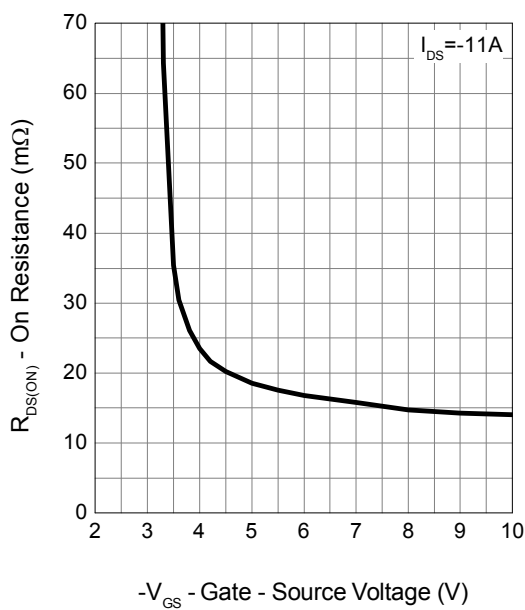
Output Characteristics



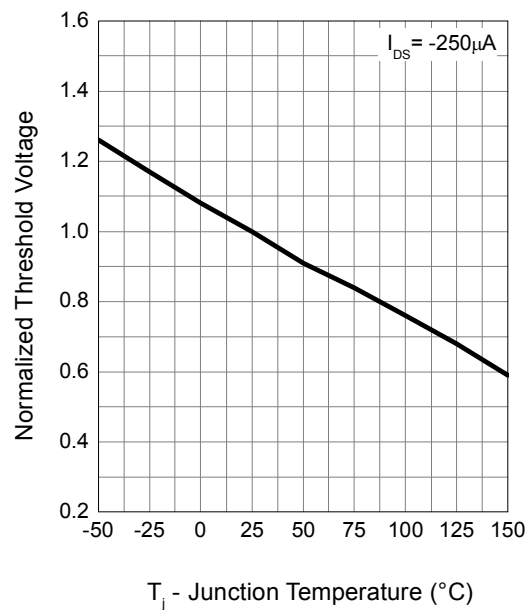
Drain-Source On Resistance



Gate-Source On Resistance

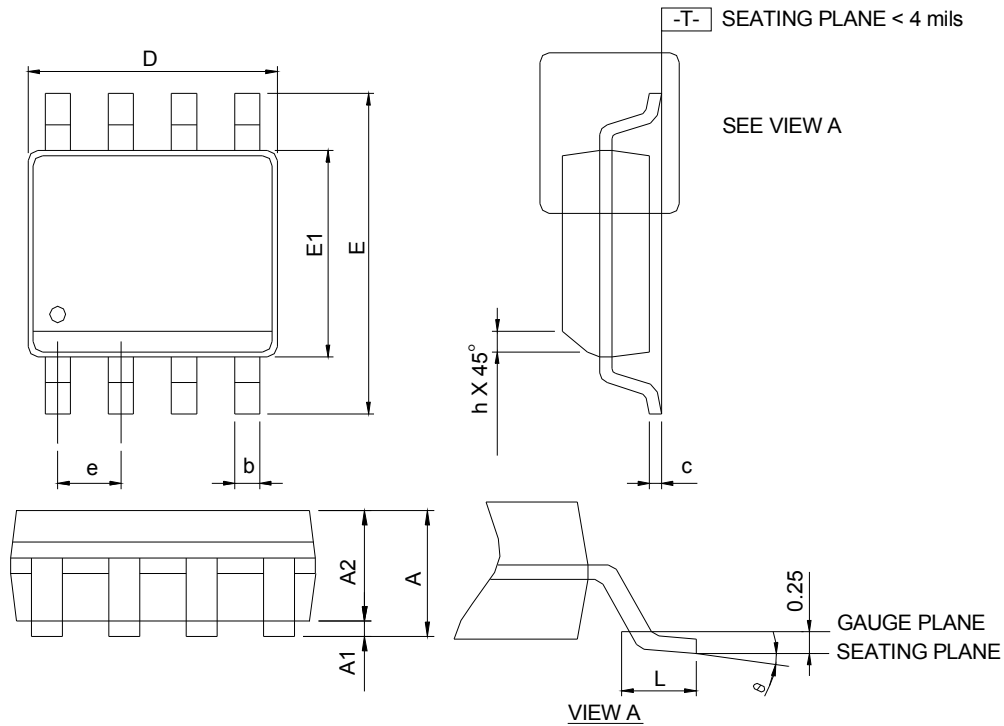


Gate Threshold Voltage



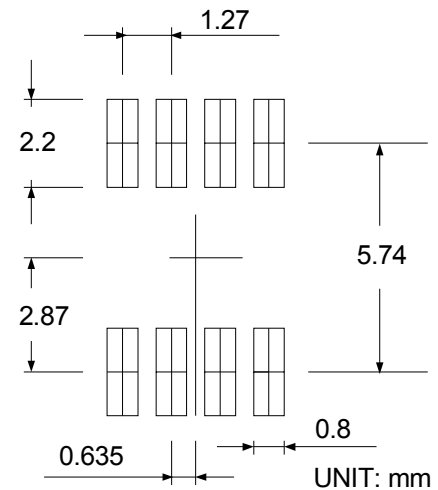
Package Information

SOP-8



DIMENSIONS	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.75		0.069
A1	0.10	0.25	0.004	0.010
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



Note: 1. Follow JEDEC MS-012 AA.

- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
- Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.



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